

EE315 - Electronics Laboratory

Experiment - 3

BJT Transistor and DC Biasing

Preliminary Work

1. For the circuit given in Figure 1

a) Calculate the value of R_{adj} that makes V_{CE} equal to 5 V.

b) Calculate V_{RB} (voltage drop across R_B).

c) Explain the reason for choosing V_{CE} equal to 5 V.

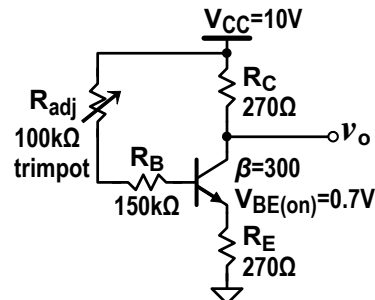


Figure 1. Emitter-stabilized bias circuit

2. For the circuit given in Figure 2, determine I_B , I_C , V_B , V_E , and V_{CE} .

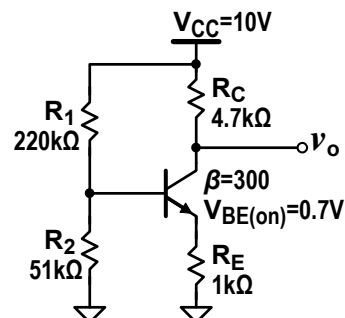


Figure 2. Voltage divider biasing circuit

3. For the circuit given in Figure 3, derive an expression for $v_O = v_C$ as a function of v_{drv} . Specify the v_{drv} levels where the transistor turns off completely ($i_C = 0$) and it goes into saturation ($i_C < \beta i_B$).

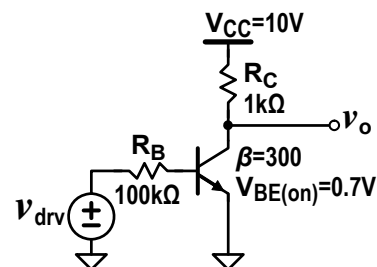


Figure 3. Switching circuit

4. For the circuit given in Figure 4, find the values of R_C and R_B , so that $I_{Csat} = 2 \text{ mA}$ and v_O changes between 10 V and 0 V while v_{drv} is a 1 kHz square wave signal switching between 0 V and 10 V.

Draw v_{drv} and v_O as a function of time.

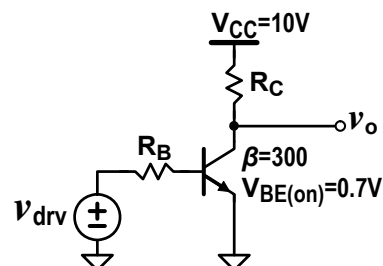


Figure 4. Switching circuit

Procedure

1. Build the circuit given in Figure 1. Turn on the power supply on and adjust R_{adj} so that V_{CE} is 5 V.

1.a) Measure V_{BE} and the voltages across R_B , and R_C while V_{CE} is still at 5 V. Measure the resistance values for R_{adj} , R_B , R_C , and R_E . Calculate I_B , I_C , and β based on your measurements.

$V_{BE} =$ $V_{RB} =$ $V_{RC} =$
 $R_{adj} =$ $R_B =$ $R_C =$ $R_E =$
 $I_B =$ $I_C =$ $\beta =$

1.b) Which value(s) among R_B , R_C , R_E , β , and $V_{BE(on)}$ is/are the most significant cause of error between the calculated and measured values of R_{adj} ?

2.a) Build the circuit in Figure 2. Measure the values of I_B , I_C , V_B , V_{BE} , and V_{CE} .

2.b) Replace the transistor with another transistor with the same part number (i.e. replace BC238 with another BC238) and repeat the measurements.

Measurement	1st Transistor	2nd Transistor
I_C		
I_B		
V_B		
V_{BE}		
V_{CE}		

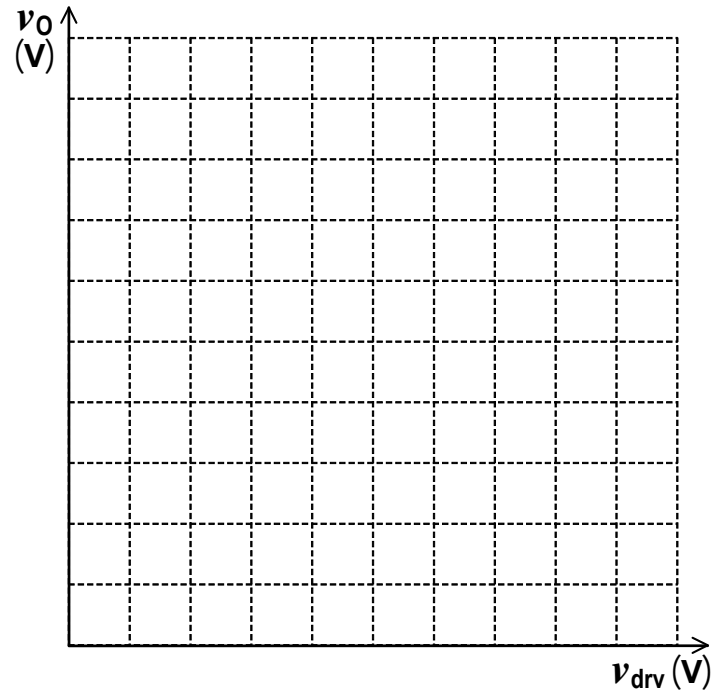
2.c) In practice, all component values are specified with a tolerance range. Tolerance range determines the minimum and maximum of the actual values that will be obtained if several of these components are tested. For example, a **100 k Ω** resistor with **5 %** tolerance may have an actual value between **95 k Ω** and **105 k Ω** . Similarly, the minimum and maximum values of β are given in transistor datasheets.

If thousands of this circuit are to be manufactured, then you had to make sure that V_{CE} will be reasonable within the tolerance range of all components. Indicate in the table below, which end ("**min**" or "**max**") of the tolerance range should be used for each parameter in calculation of the lowest and highest values of V_{CE} .

Component parameter	For lowest V_{CE}	For highest V_{CE}
R_1		
R_2		
R_C		
R_E		
β		
$V_{BE(on)}$		

3.a) Build the circuit given in Figure 3. Increase v_{drv} slowly, from **0V** up to the value where v_o becomes constant. Record at least 10 values in order to plot a v_o versus v_{drv} graph.

v_{drv} (V)	v_o (V)



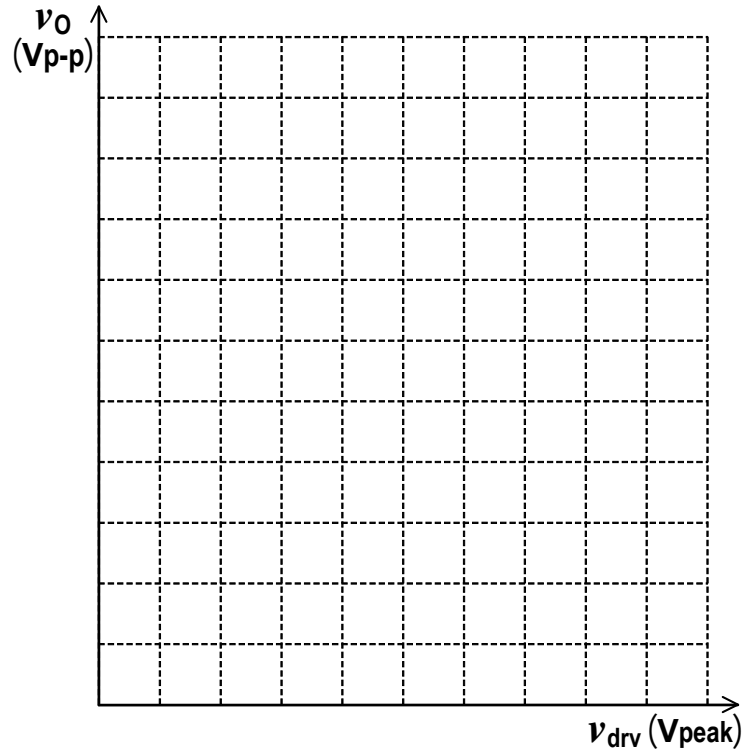
3.b) Measure the range of v_{drv} values in which the transistor acts as a switch.

$v_{drv-Low-Max} =$ (where $v_o > 90\%$ of V_{CC})

$v_{drv-High-Min} =$ (where $v_o < 10\%$ of V_{CC})

4.a) Setup the circuit in Figure 4 using the R_B and R_C values previously calculated in the preliminary work. Observe and plot V_O (Vp-p) versus V_{drv} (Vpeak) for different frequency and amplitude settings of input signal. Choose a range of V_{drv} values to cover the minimum and maximum possible V_O amplitudes at **10 kHz** in your measurements. Use two more frequency settings where the V_O amplitude decreases by **20 %** and **50 %** at the maximum V_{drv} value used at **10 kHz**.

Freq. (kHz)	V_{drv} (Vpeak)	V_O (Vp-p)
10		



4.b) Comment on the difference in the output signals resulting from the changes in input parameters.